## SIEMENS

## Silicon Switching Diode Array

BAV 70

- For high-speed switching
- Common cathode


| Type | Marking | Ordering Code <br> (tape and reel) | Pin Configuration | Package ${ }^{\text {1) }}$ |
| :--- | :--- | :--- | :--- | :--- |
| BAV 70 | A4s | Q68000-A6622 |  | SOT-23 |
|  |  |  | 0 | 0 |

## Maximum Ratings per Diode

| Parameter | Symbol | Values | Unit |
| :--- | :--- | :--- | :--- |
| Reverse voltage | $V_{\mathrm{R}}$ | 70 | V |
| Peak reverse voltage | $V_{\mathrm{RM}}$ | 70 |  |
| Forward current | $I_{\mathrm{F}}$ | 200 | mA |
| Surge forward current, $t=1 \mu \mathrm{~S}$ | $I_{\mathrm{Fs}}$ | 4.5 | A |
| Total power dissipation, $T \mathrm{~s}=35^{\circ} \mathrm{C}$ | $P_{\text {tot }}$ | 250 | mW |
| Junction temperature | $T_{\mathrm{J}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature range | $T_{\text {stg }}$ | $-65 \ldots+150$ |  |

## Thermal Resistance

| Junction - ambient ${ }^{2}$ ) | $R_{\text {th JA }}$ | $\leq 600$ | K/W |
| :--- | :--- | :--- | :--- |
| Junction - soldering point | $R_{\text {th Js }}$ | $\leq 460$ |  |

[^0]
## Electrical Characteristics per Diode

at $T_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise specified.

| Parameter | Symbol | Values |  |  | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- |
|  |  | min. | typ. | max. |  |

## DC characteristics

| Breakdown voltage <br> $I_{(\mathrm{BR})}=100 \mu \mathrm{~A}$ | $V_{(\mathrm{BR})}$ | 70 | - | - | V |
| :--- | :--- | :--- | :--- | :--- | :--- |
| Forward voltage | $V_{\mathrm{F}}$ |  |  |  | mV |
| $I_{\mathrm{F}}=1 \mathrm{~mA}$ |  | - | - | 715 |  |
| $I_{\mathrm{F}}=10 \mathrm{~mA}$ |  | - | - | 855 |  |
| $I_{\mathrm{F}}=50 \mathrm{~mA}$ |  | - | - | 1000 |  |
| $I_{\mathrm{F}}=150 \mathrm{~mA}$ |  | $I_{\mathrm{R}}$ |  |  |  |
| Reverse current |  | - | - | 2.5 | $\mu \mathrm{~A}$ |
| $V_{\mathrm{R}}=70 \mathrm{~V}$ | - | - | 30 |  |  |
| $V_{\mathrm{R}}=25 \mathrm{~V}, T_{\mathrm{A}}=150^{\circ} \mathrm{C}$ |  | - | - | 50 |  |
| $V_{\mathrm{R}}=70 \mathrm{~V}, T_{\mathrm{A}}=150^{\circ} \mathrm{C}$ |  |  |  |  |  |

## AC characteristics

| Diode capacitance <br> $V_{\mathrm{R}}=0 \mathrm{~V}, f=1 \mathrm{MHz}$ | $C \mathrm{D}$ | - | - | 1.5 | pF |
| :--- | :--- | :--- | :--- | :--- | :--- |
| Reverse recovery time <br> $I_{\mathrm{F}}=10 \mathrm{~mA}, I_{\mathrm{R}}=10 \mathrm{~mA}, R \mathrm{~L}=100 \Omega$ <br> measured at $I_{\mathrm{R}}=1 \mathrm{~mA}$ | $\mathrm{trr}_{\mathrm{r}}$ | - | - | 6 | ns |

Test circuit for reverse recovery time


Pulse generator: $t_{\mathrm{p}}=100 \mathrm{~ns}, D=0.05$

$$
t_{\mathrm{r}}=0.6 \mathrm{~ns}, R_{\mathrm{j}}=50 \Omega
$$

Oscillograph: $\quad R=50 \Omega$
$t_{\mathrm{r}}=0.35 \mathrm{~ns}$
$C \leq 1 \mathrm{pF}$

Forward current $I_{F}=f\left(T_{\mathrm{A}^{*}} ; T_{\mathrm{s}}\right)$

* Package mounted on epoxy


Forward current $I F=f\left(V_{F}\right)$
$T_{\mathrm{A}}=25^{\circ} \mathrm{C}$


Reverse current $I_{\mathrm{R}}=f\left(T_{\mathrm{A}}\right)$


Peak forward current $I_{F M}=f(t)$
$T_{\mathrm{A}}=25^{\circ} \mathrm{C}$


## Forward voltage $V_{F}=f\left(T_{\mathrm{A}}\right)$




[^0]:    1) For detailed information see chapter Package Outlines.
    2) Package mounted on epoxy pcb $40 \mathrm{~mm} \times 40 \mathrm{~mm} \times 1.5 \mathrm{~mm} / 6 \mathrm{~cm}^{2}$.
